



IGBT Discrete

V_{CE}	1200	V
I_C	25	A
$V_{CE(SAT)}$ $I_C=25A$	1.85	V

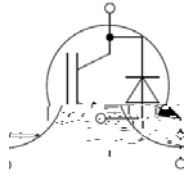
Applications

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-
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Features

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Circuit



Maximum Ratings

Parameter	Symbol	Value	Unit



DGW25N120CTL

Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						



DGW25N120CTL

Electrical Characteristics of the Diode

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						



DGW25N120CTL

Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at $T_j = 25$						



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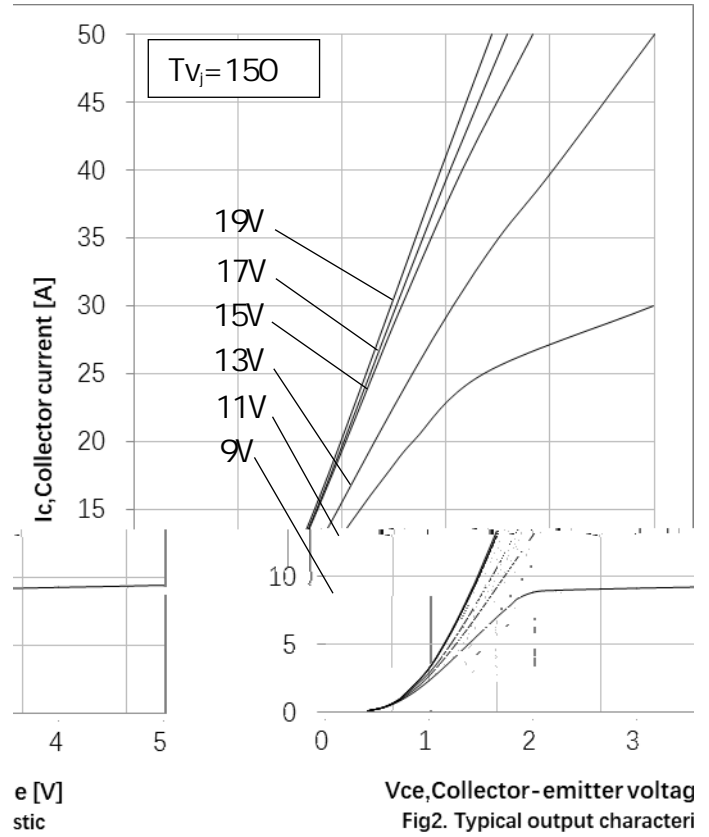
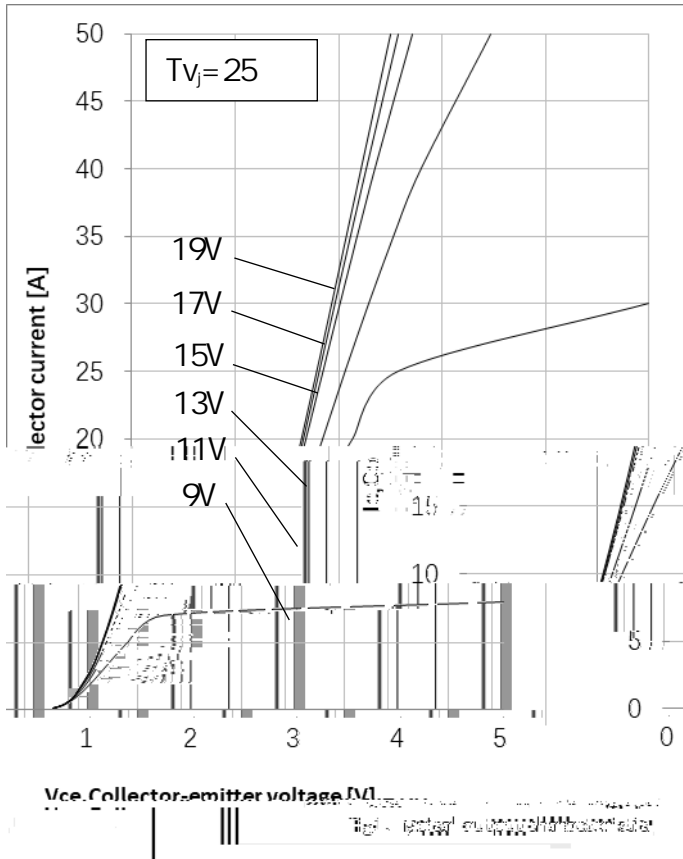


Fig2. Typical output characteristics

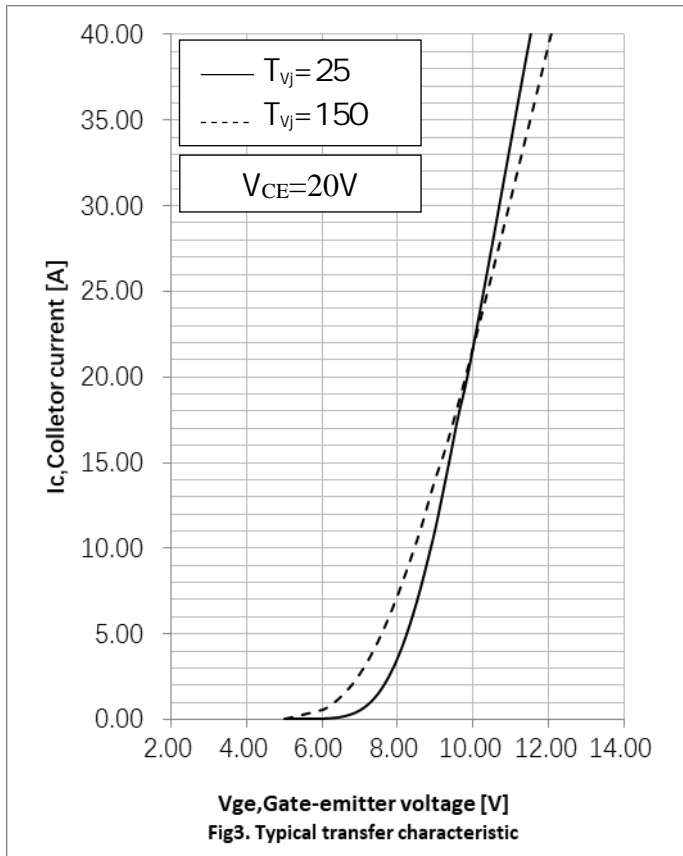


Fig3. Typical transfer characteristic

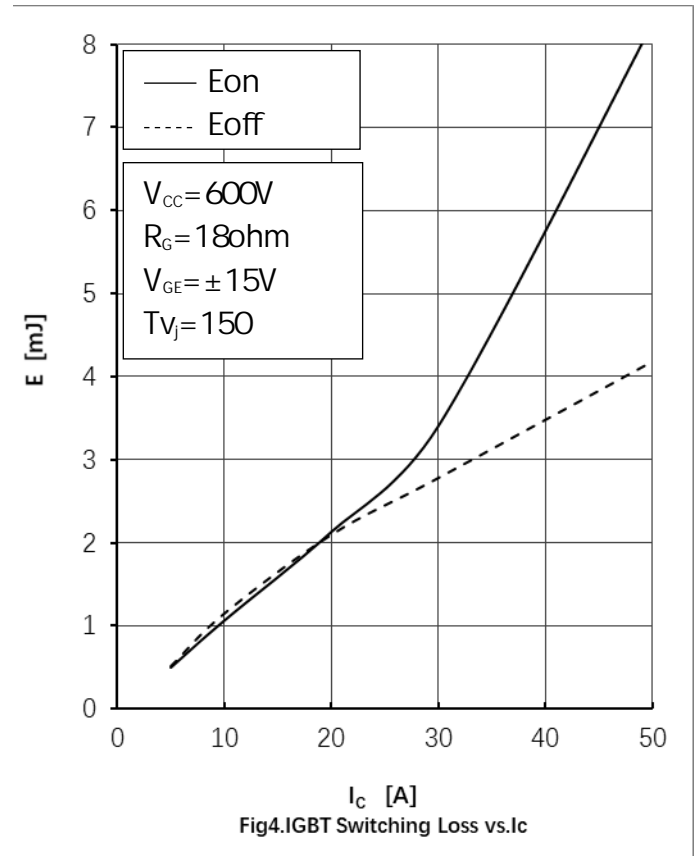
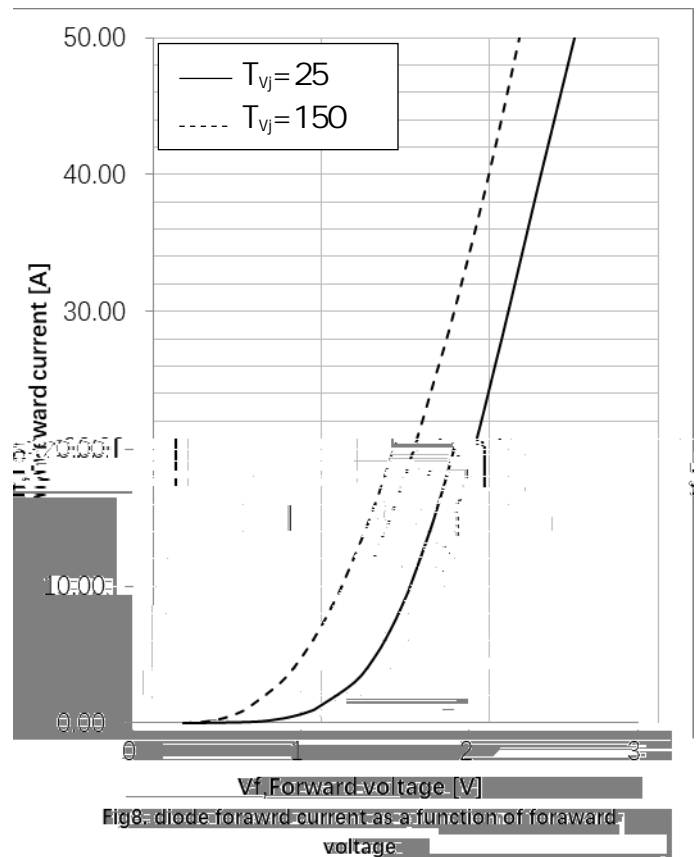
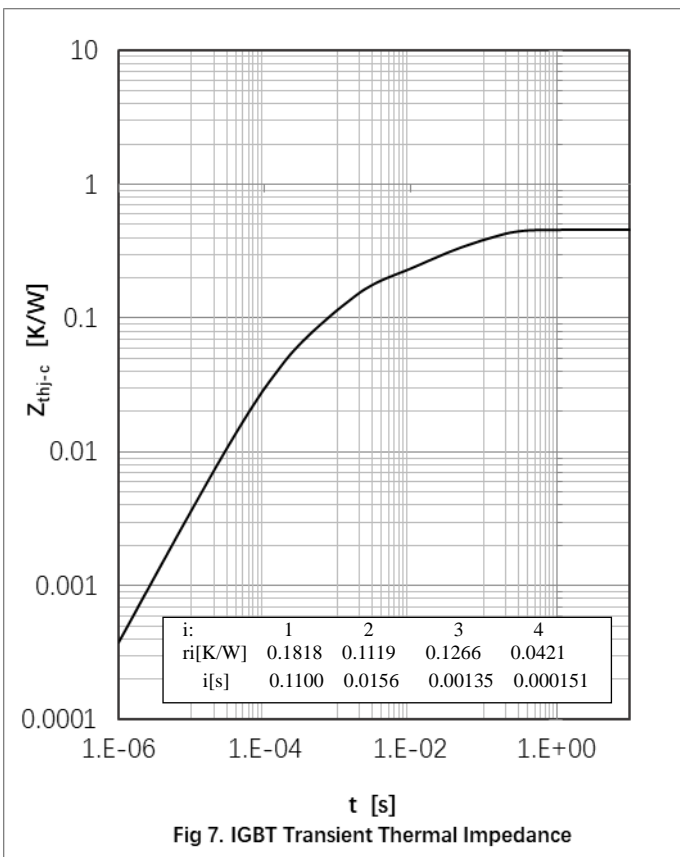
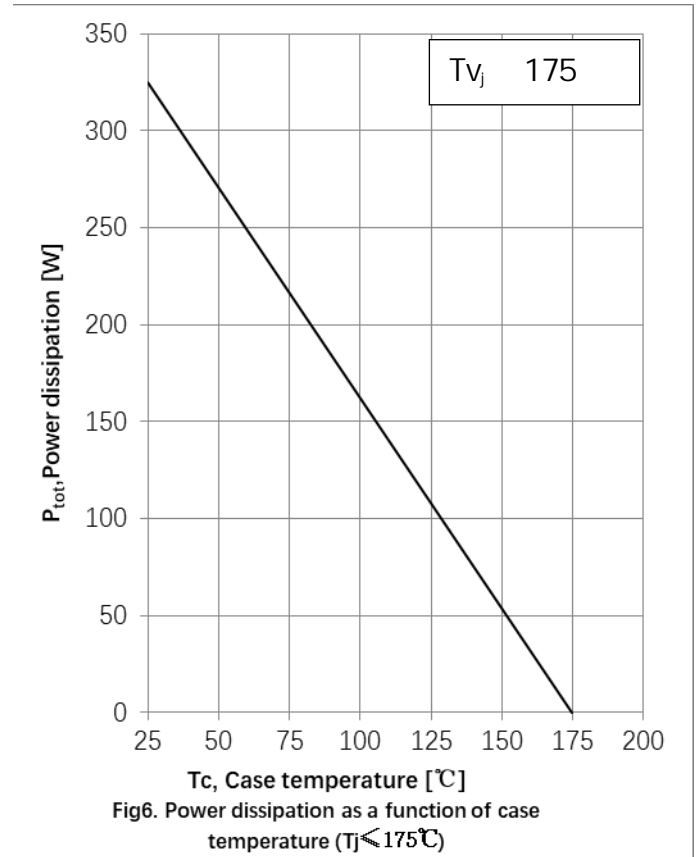
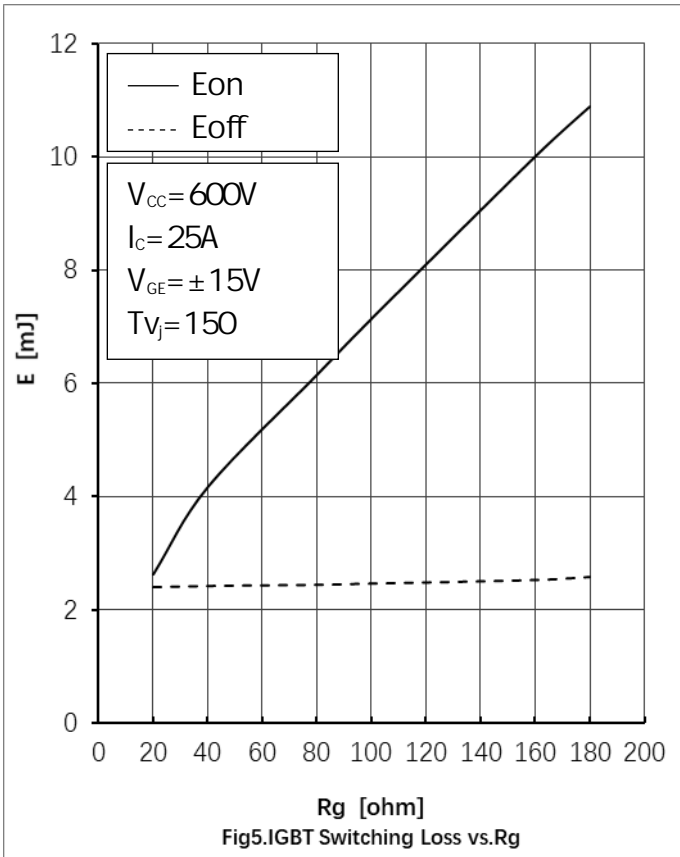


Fig4. IGBT Switching Loss vs. Ic



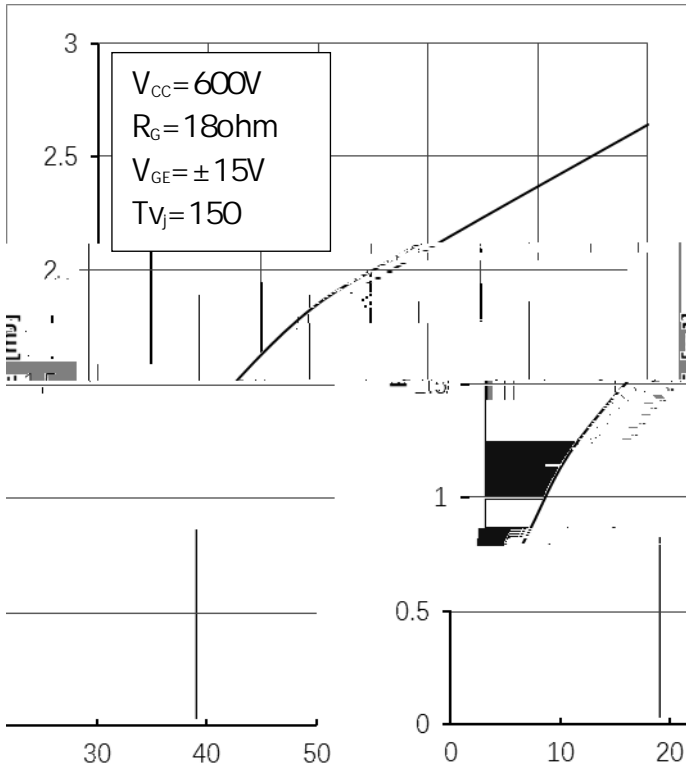


Fig9. Diode Switching Loss(Erec) vs. I_F

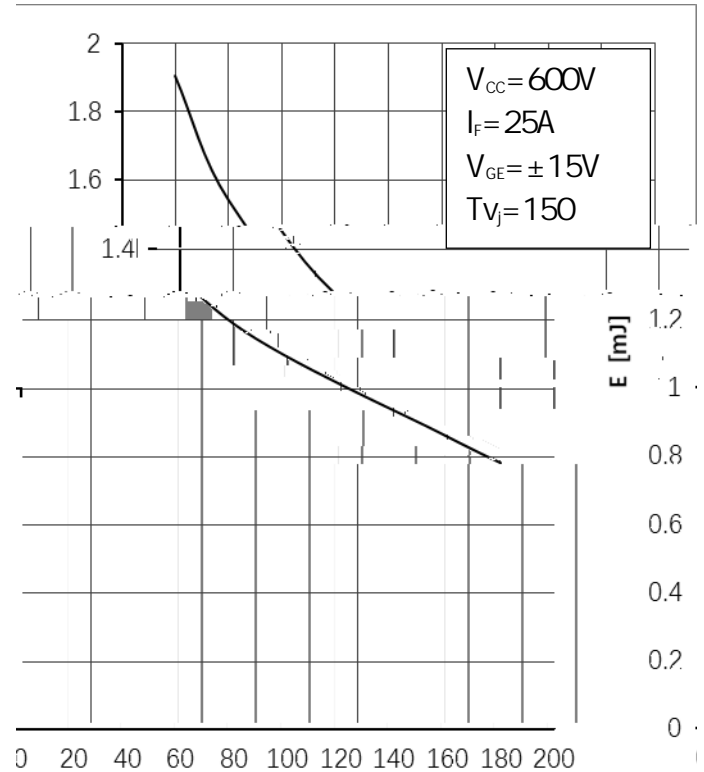


Fig10. Diode Switching Loss(Erec) vs. R_g

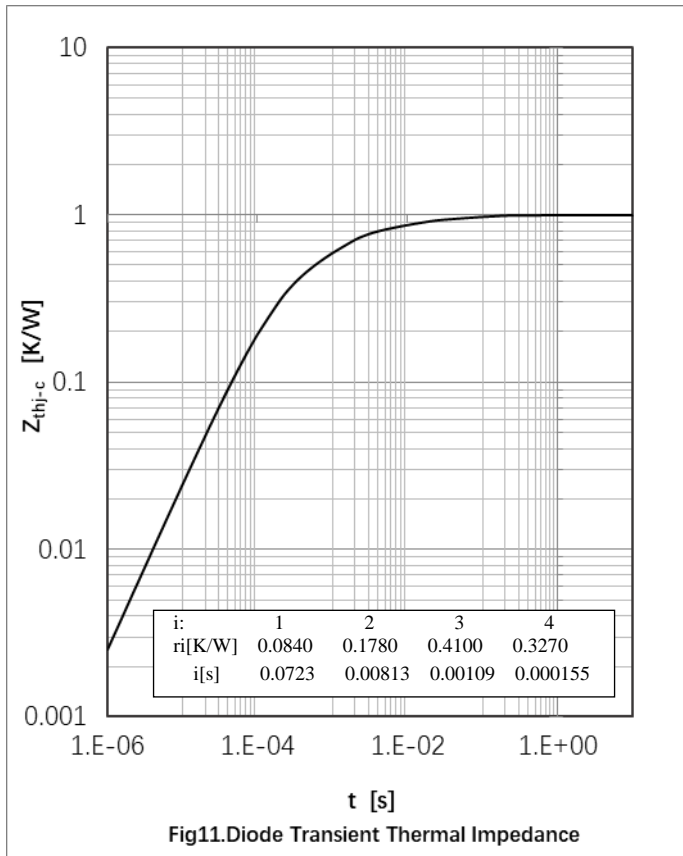
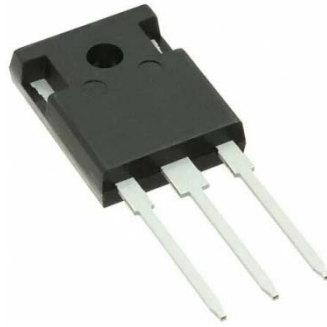
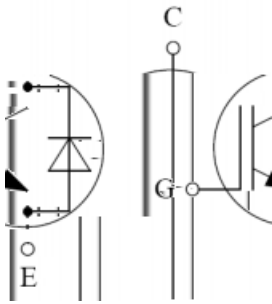


Fig11. Diode Transient Thermal Impedance



DGW25N120CTL

Circuit Diagram



Package Outline Information

CASE: TO 247

